

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C6

650V CoolMOS™ C6 Power Transistor
IPL65R1K0C6S

Data Sheet

Rev. 2.0
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

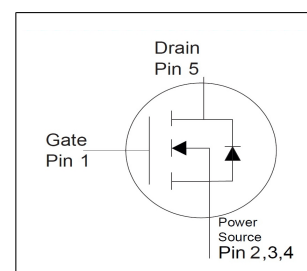
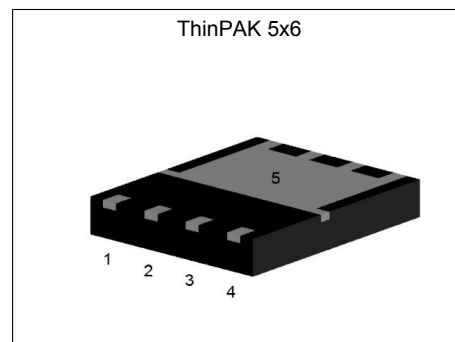


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	1	Ω
$Q_{g,typ}$	15	nC
$I_{D,pulse}$	12.3	A
$E_{oss@400V}$	1.5	μJ
Body diode di/dt	500	A/ μs

Type / Ordering Code	Package	Marking	Related Links
IPL65R1K0C6S	ThinPAK 5x6 SMD	65C61K0	see Appendix A

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	4.2 2.7	A	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	12.3	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	50	mJ	$I_D = 1\text{A}$; $V_{DD} = 50\text{V}$
Avalanche energy, repetitive	E_{AR}	-	-	0.15	mJ	$I_D = 1\text{A}$; $V_{DD} = 50\text{V}$
Avalanche current, repetitive	I_{AR}	-	-	1.0	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 520\text{V}$
Gate source voltage	V_{GS}	-20 -30	-	20 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation (non FullPAK)	P_{tot}	-	-	34.7	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	T_j, T_{stg}	-40	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	3.7	A	$T_C = 25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	10.8	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$
Maximum diode commutation speed ³⁾	di/dt	-	-	500	A/ μs	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$

3 Thermal characteristics

Table 3 Thermal characteristics (non FullPAK)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.6	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient	R_{thJA}	-	35	62	$^\circ\text{C/W}$	Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm ² (one layer 70 μm thick) copper area for drain connection and cooling. PCB is vertical without blown air.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL1

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ $V_{DClk}=400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.50	3	3.50	V	$V_{DS}=V_{GS}$, $I_D=0.15mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650V$, $V_{GS}=0V$, $T_j=25^\circ C$ $V_{DS}=650V$, $V_{GS}=0V$, $T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.90	1.00	Ω	$V_{GS}=10V$, $I_D=1.5A$, $T_j=25^\circ C$ $V_{GS}=10V$, $I_D=1.5A$, $T_j=150^\circ C$
Gate resistance	R_G	-	5.5	-	Ω	$f=1\text{ MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	328	-	pF	$V_{GS}=0V$, $V_{DS}=100V$, $f=1MHz$
Output capacitance	C_{oss}	-	23	-	pF	$V_{GS}=0V$, $V_{DS}=100V$, $f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	14	-	pF	$V_{GS}=0V$, $V_{DS}=0...520V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	58.5	-	pF	$I_D=constant$, $V_{GS}=0V$, $V_{DS}=0...520V$
Turn-on delay time	$t_{d(on)}$	-	6.6	-	ns	$V_{DD}=400V$, $V_{GS}=10V$, $I_D=2.2A$, $R_G=10.2\Omega$
Rise time	t_r	-	5.2	-	ns	$V_{DD}=400V$, $V_{GS}=10V$, $I_D=2.2A$, $R_G=10.2\Omega$
Turn-off delay time	$t_{d(off)}$	-	41	-	ns	$V_{DD}=400V$, $V_{GS}=10V$, $I_D=2.2A$, $R_G=10.2\Omega$
Fall time	t_f	-	13.6	-	ns	$V_{DD}=400V$, $V_{GS}=10V$, $I_D=2.2A$, $R_G=10.2\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.8	-	nC	$V_{DD}=520V$, $I_D=2.2A$, $V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	8	-	nC	$V_{DD}=520V$, $I_D=2.2A$, $V_{GS}=0$ to 10V
Gate charge total	Q_g	-	15	-	nC	$V_{DD}=520V$, $I_D=2.2A$, $V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	5.3	-	V	$V_{DD}=520V$, $I_D=2.2A$, $V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$
²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=2.2A$, $T_i=25^{\circ}C$
Reverse recovery time	t_{rr}	-	226	-	ns	$V_R=400V$, $I_F=2.2A$, $di_F/dt=100A/\mu s$
Reverse recovery charge	Q_{rr}	-	1.3	-	μC	$V_R=400V$, $I_F=2.2A$, $di_F/dt=100A/\mu s$
Peak reverse recovery current	I_{rrm}	-	9.9	-	A	$V_R=400V$, $I_F=2.2A$, $di_F/dt=100A/\mu s$

5 Electrical characteristics diagrams

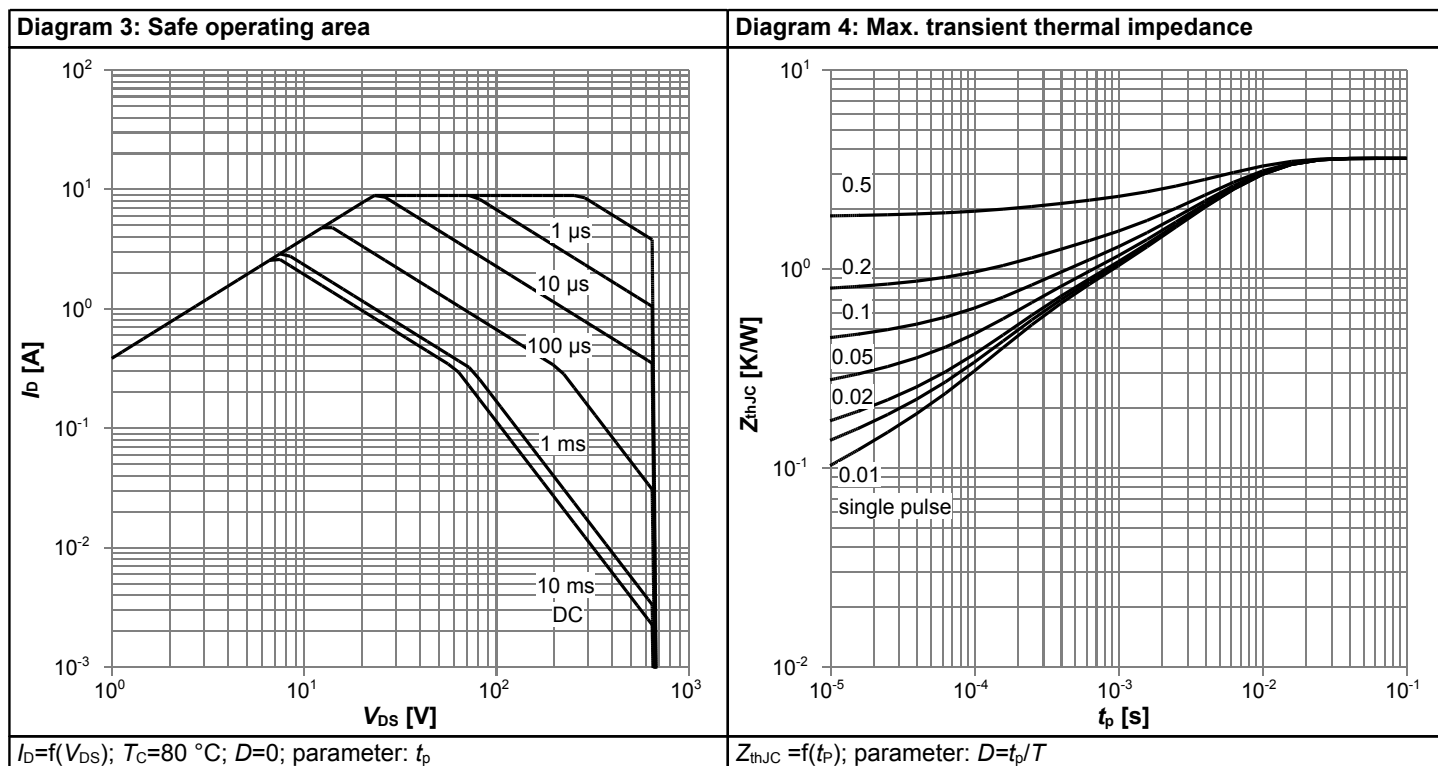
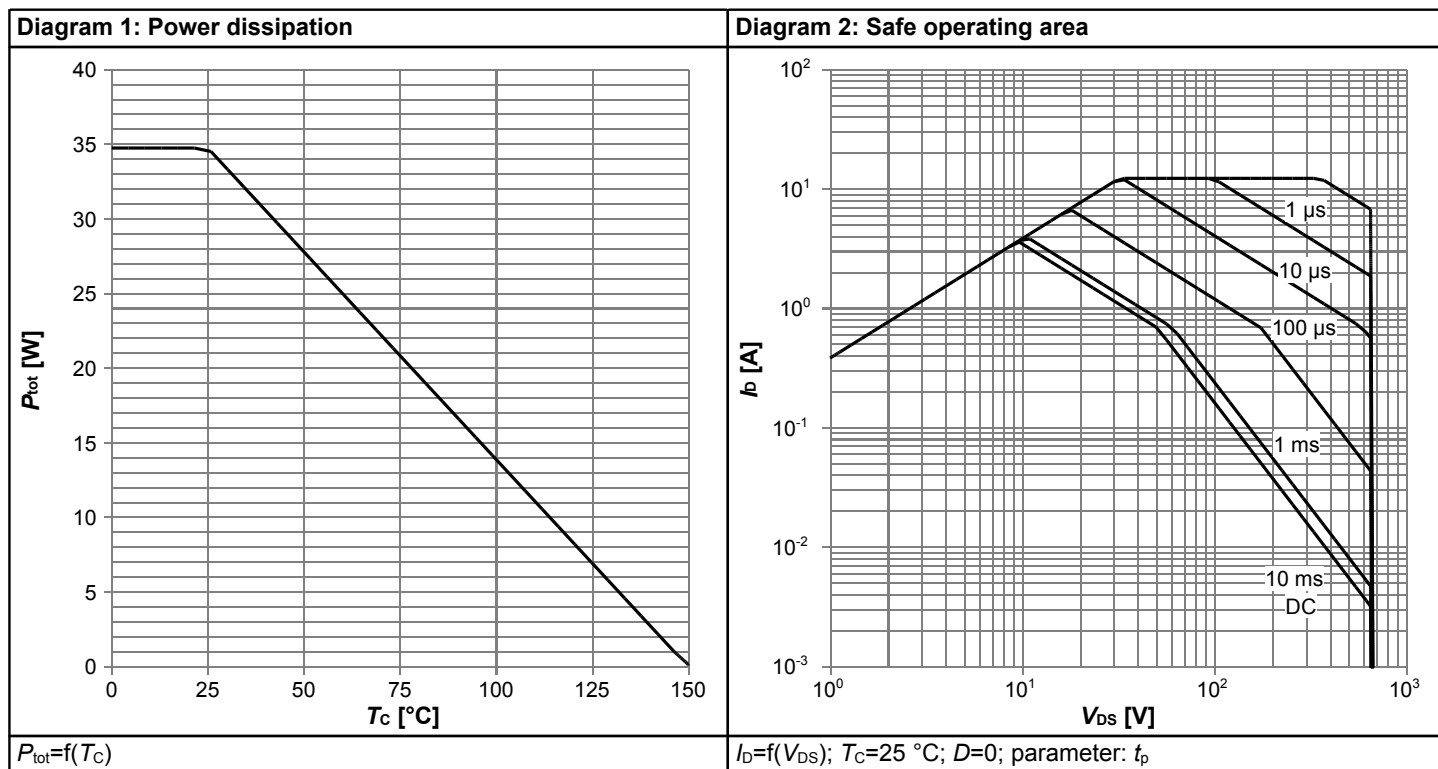


Diagram 5: Typ. output characteristics

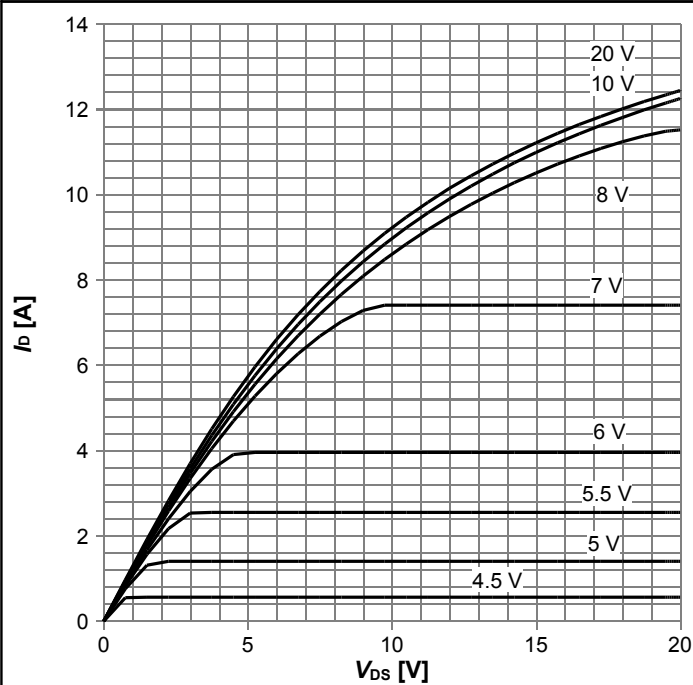

 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics

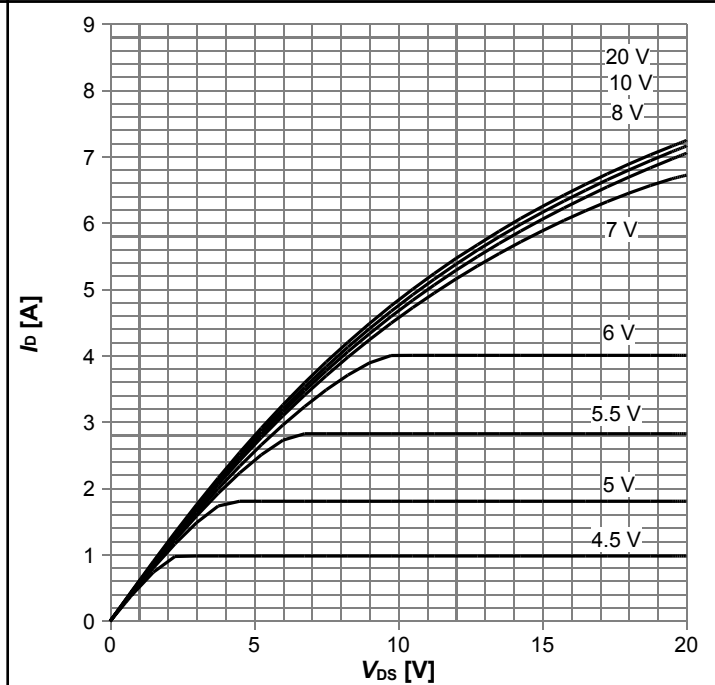

 $I_D = f(V_{DS}); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance

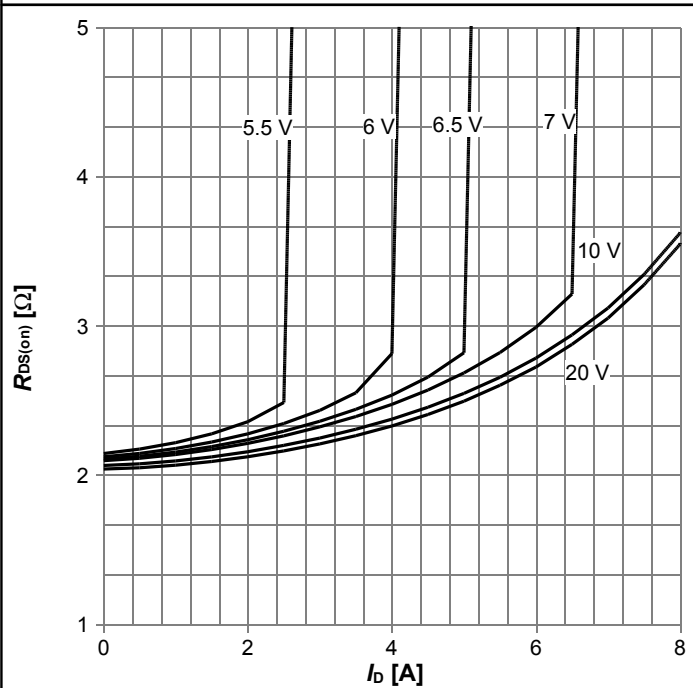

 $R_{DS(on)} = f(I_D); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance

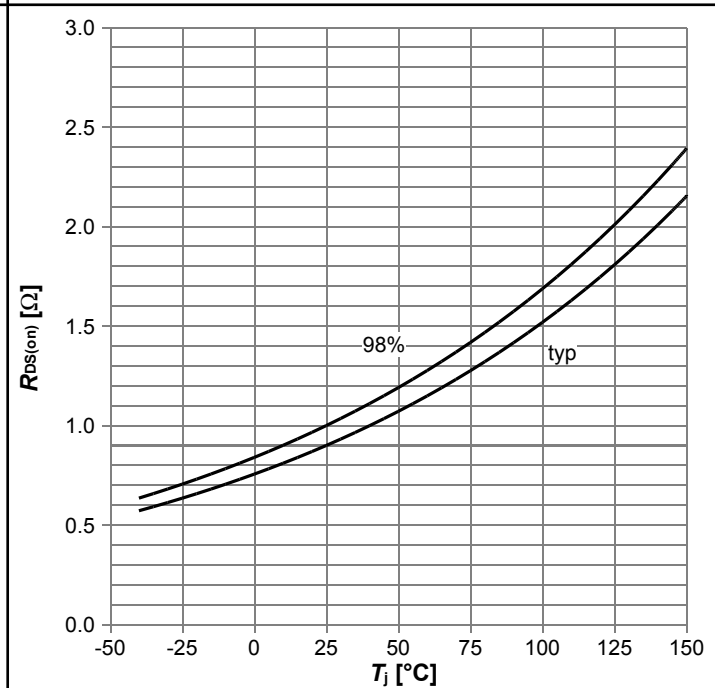

 $R_{DS(on)} = f(T_J); I_D = 1.5\text{ A}; V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics

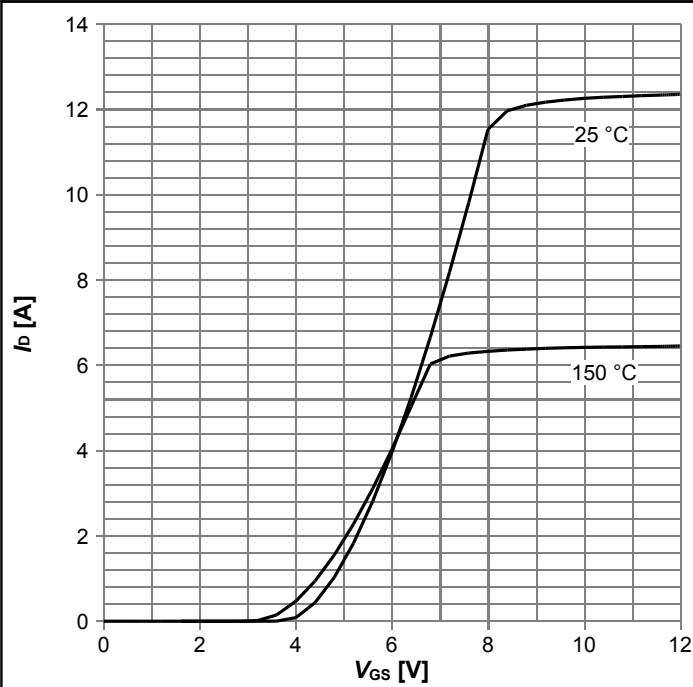

 $I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge

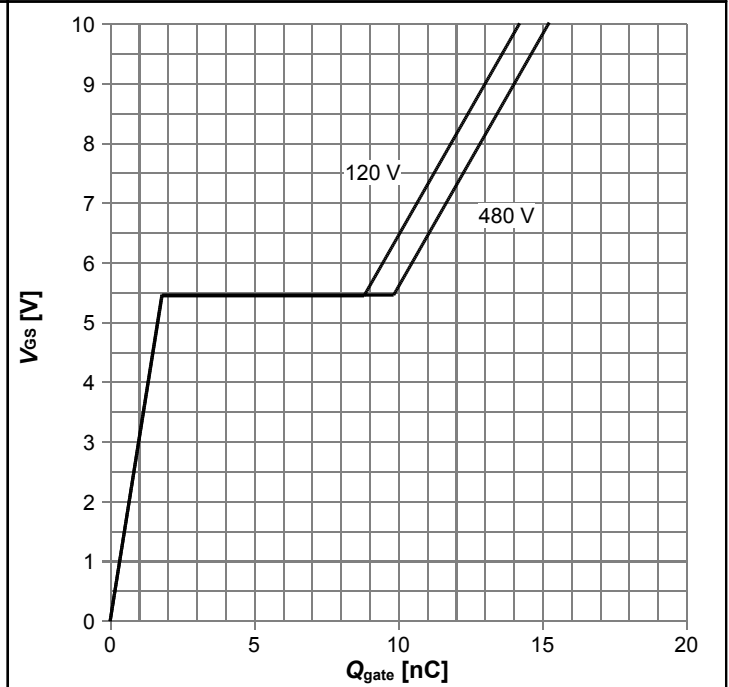

 $V_{GS} = f(Q_{gate}); I_D = 2.2 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode

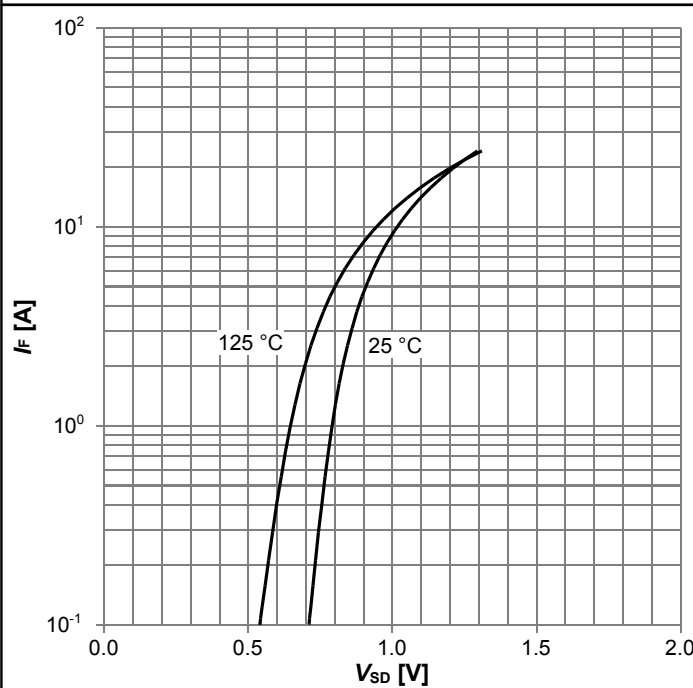

 $I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy

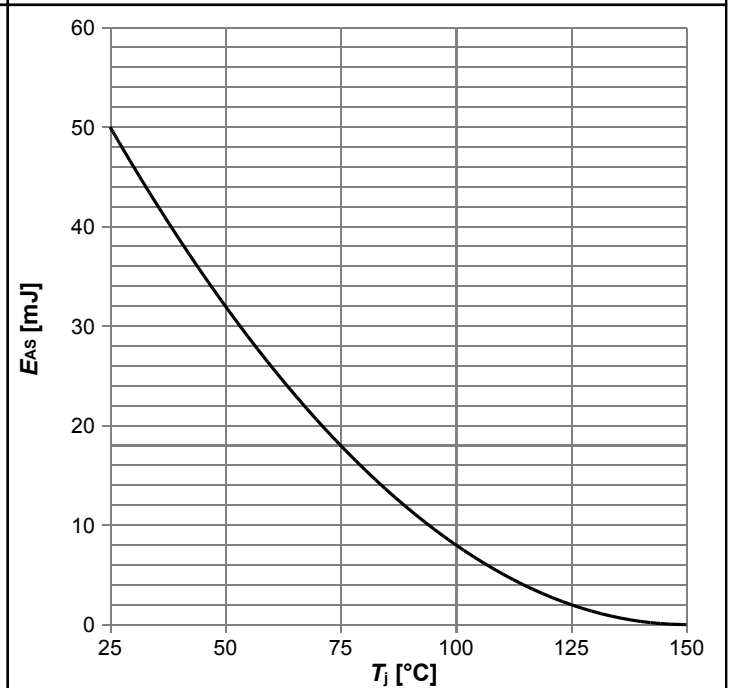
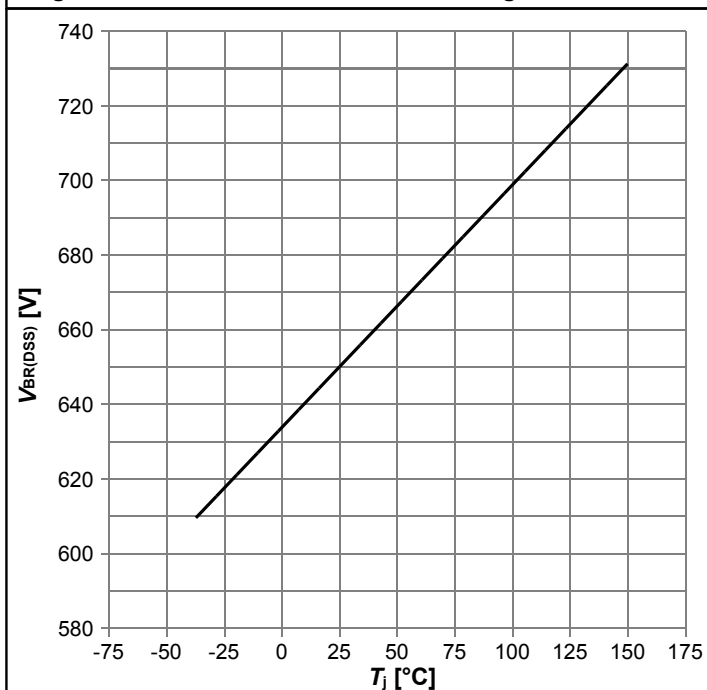
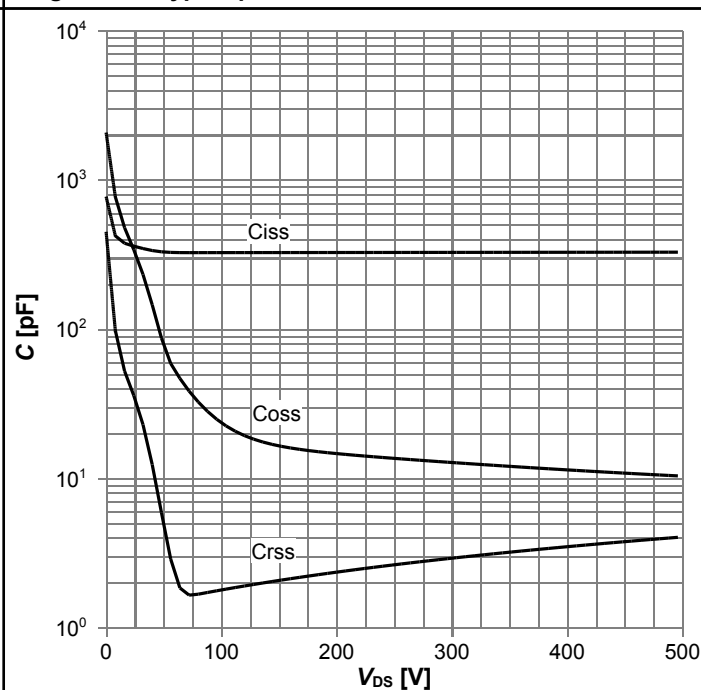

 $E_{AS} = f(T_j); I_D = 1 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 13: Drain-source breakdown voltage



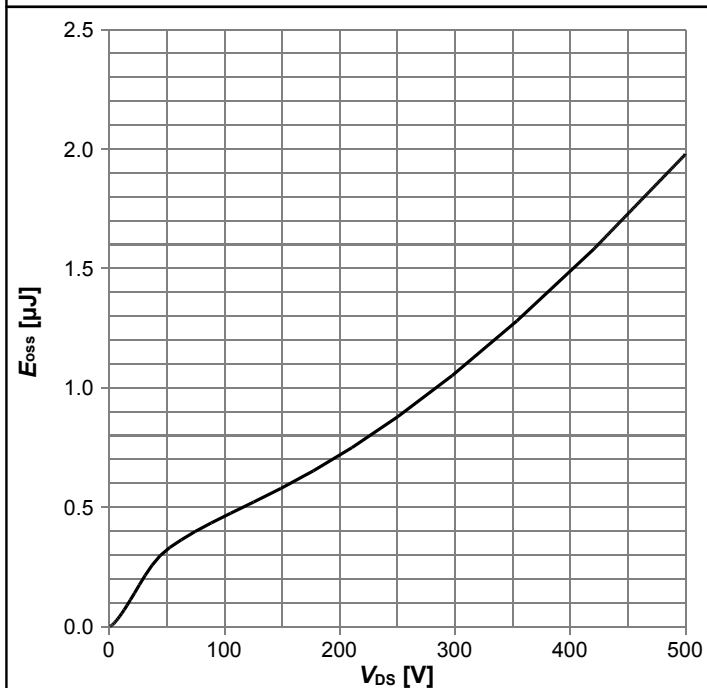
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 8 Diode characteristics

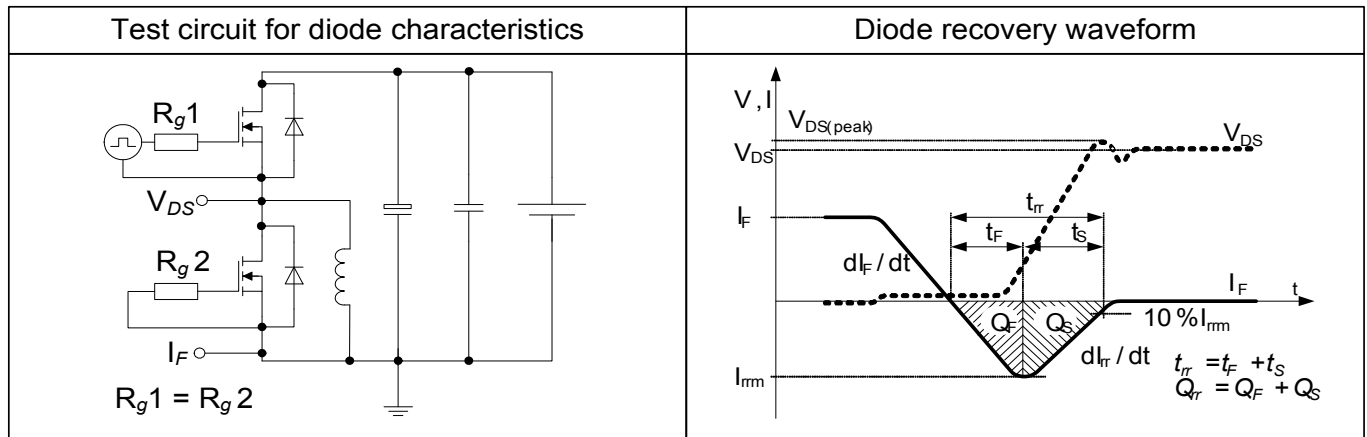


Table 9 Switching times

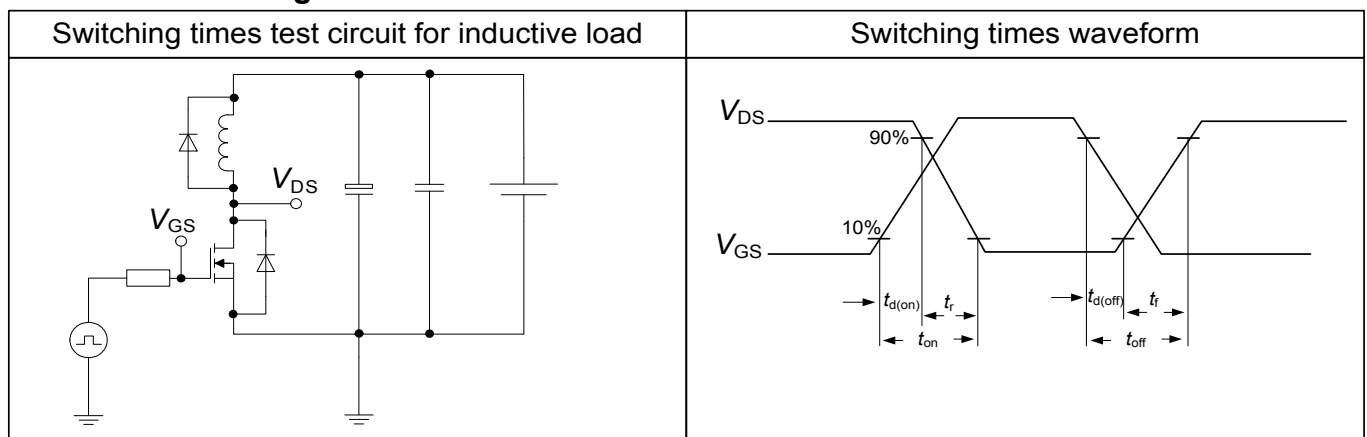
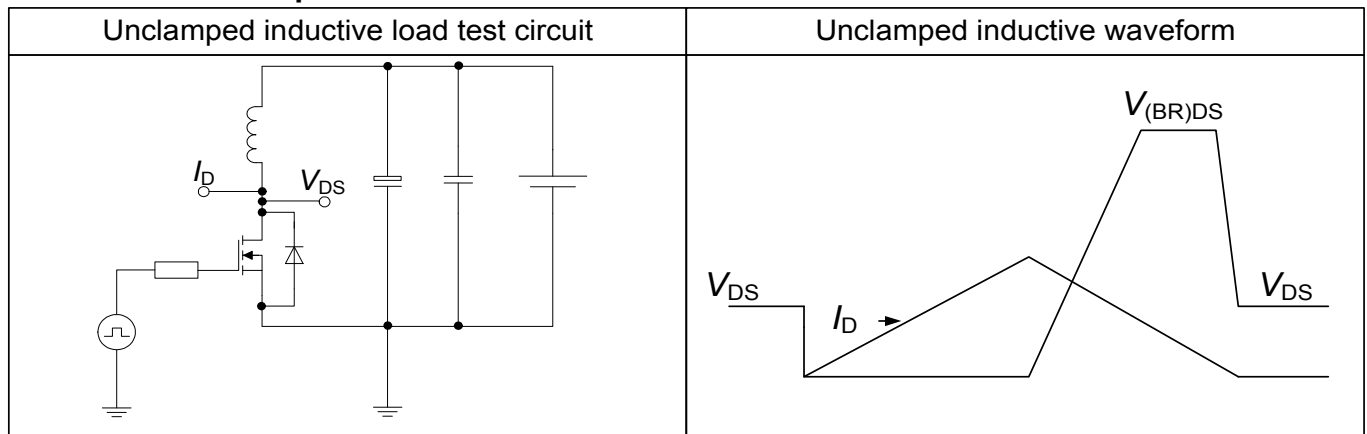


Table 10 Unclamped inductive load



7 Package Outlines

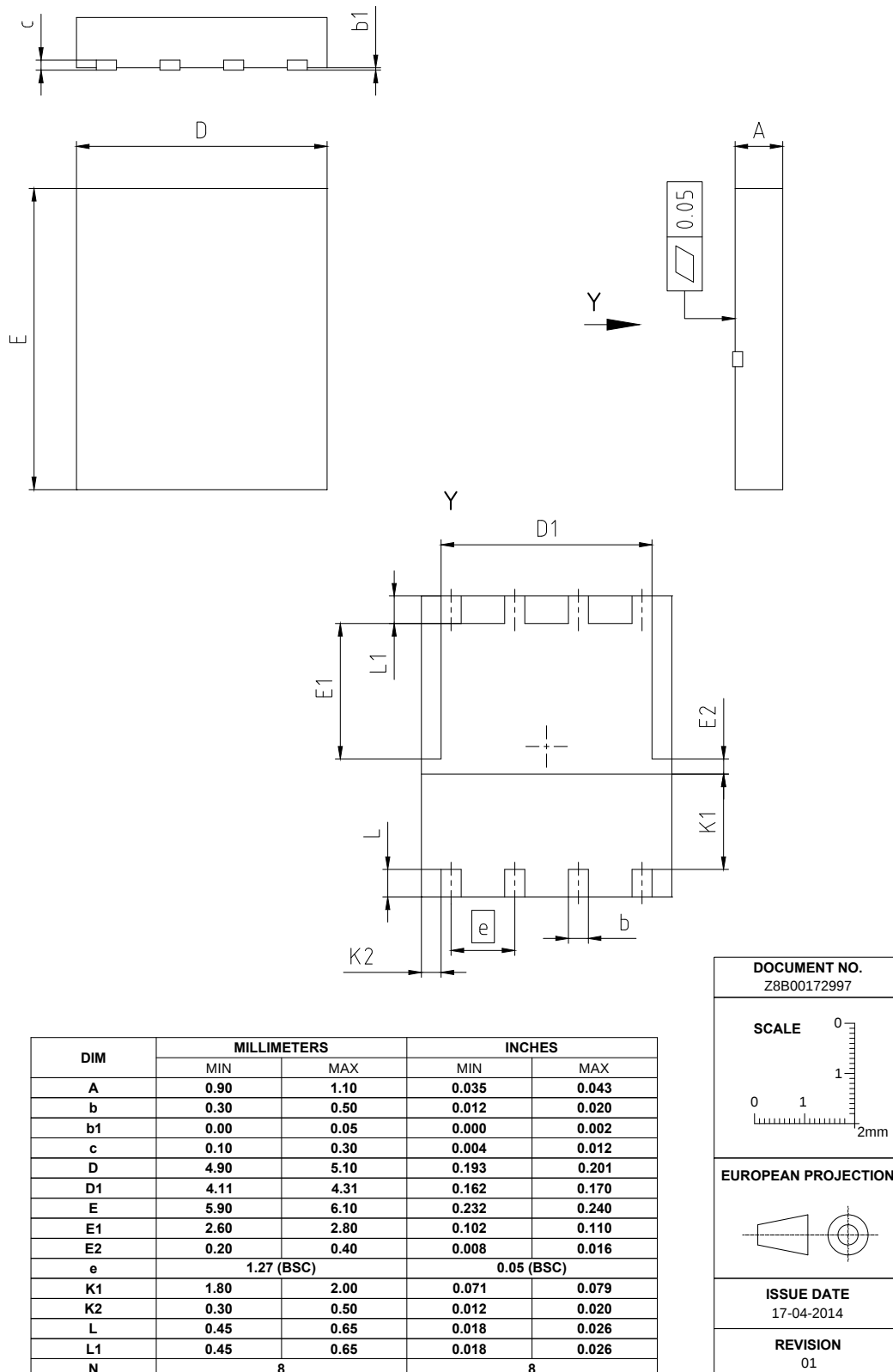


Figure 1 Outline ThinPAK 5x6 SMD, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- IFX CoolMOS Webpage: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPL65R1K0C6S

Revision: 2014-07-08, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-07-08	Release of final version

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